Ordering number : EN1879B

SANYO No.1879B

DTM8-N

Silicon Planar Type

8A Bidirectional Thyristor

Features

- Insulation type
- Peak OFF-state voltage : 200 to 600V
- RMS ON-state current : 8A
- TO-220 package

Absolute Maximum Ratings at Ta = 25°C

			CDTM 8C-N	DTM 8E-N	DTM 8G-N	unit
Repetitive Peak OFF-State Voltage	V_{DRM}		200	400	600	V
RMS ON-State Current	$I_{T(RMS)}$	Tc = 83°C, single-phase full-wave	→	→	8	A
Surge ON-State Current	I_{TSM}	Peak 1 cycle, 50Hz	→	→	80	A
Amperes Squared-Seconds	$\int i^2t \cdot dt$	1ms ≦ t ≦ 10ms	→	→	32	A^2S
Peak Gate Power Dissipation	P_{GM}	f ≧ 50Hz, duty ≦ 10%	→	→	5	W
Average Gate Power Dissipation	$P_{G(AV)}$		→	→	0.5	W
Peak Gate Current	I_{GM}	f ≧ 50Hz, duty ≦ 10%	→	→	±2	A
Peak Gate Voltage	V_{GM}	f ≧ 50Hz, duty ≦ 10%	→	→	±10	V
Junction Temperature	Tj		→	→	125	°C
Storage Temperature	Tstg		→	−40 to +125		°C
Weight			→	→	2.1	g

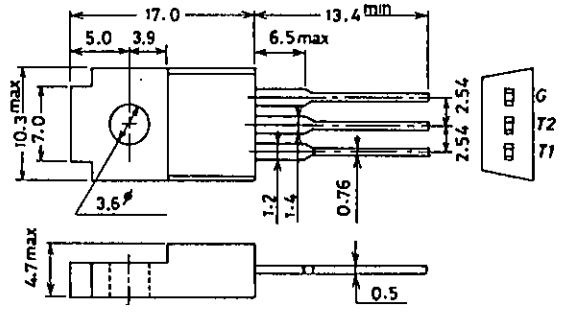
Electrical Characteristics at Ta = 25°C

				min	typ	max	unit
Repetitive Peak OFF-State Current		I_{DRM}	Tj = 125°C, $V_D = V_{DRM}$			2	mA
Peak ON-State Voltage		V_{TM}	I_{TM} = 12A			1.5	V
Critical Rate of Rise of OFF-State Voltage		(dv/dt)c	Tj = 125°C, V_D = 200V(C), 400V(E to G)	10			V/μs
Holding Current		I_H	R_L = 100Ω			50	mA
Gate Trigger Current※	(I)	I_{GT}	V_D = 12V, R_L = 20Ω			30	mA
	(II)	I_{GT}	V_D = 12V, R_L = 20Ω			30	mA
	(III)	I_{GT}	V_D = 12V, R_L = 20Ω			50	mA
	(IV)	I_{GT}	V_D = 12V, R_L = 20Ω			30	mA
Gate Trigger Voltage※	(I)	V_{GT}	V_D = 12V, R_L = 20Ω			2	V
	(II)	V_{GT}	V_D = 12V, R_L = 20Ω			2	V
	(III)	V_{GT}	V_D = 12V, R_L = 20Ω			2	V
	(IV)	V_{GT}	V_D = 12V, R_L = 20Ω			2	V
Gate Nontrigger Voltage		V_{GD}	Tc = 125°C, $V_D = V_{DRM}$	0.2			V
Thermal Resistance		Rth(j-c)	Between junction and case, AC			3.6	°C/W

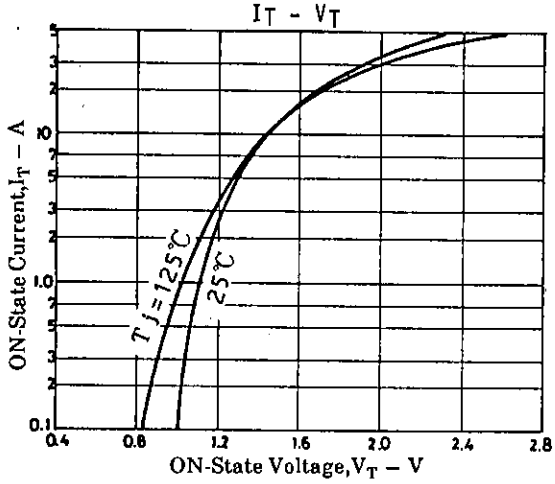
※ : The gate trigger mode is shown below.

Trigger mode	T2	T1	G
I	+	−	+
II	+	−	−
III	−	+	+
IV	−	+	−

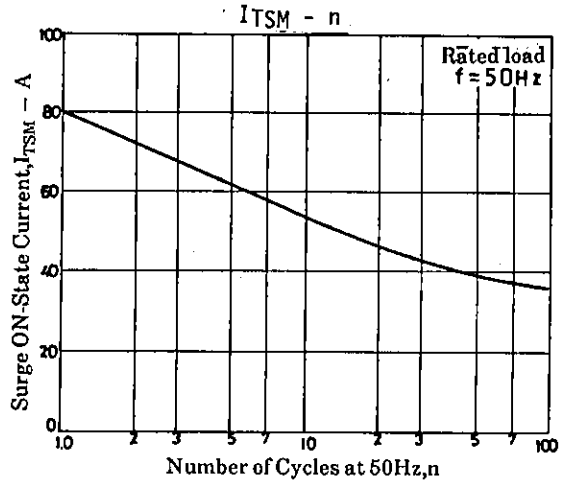
Package Dimensions 1144 (unit: mm)



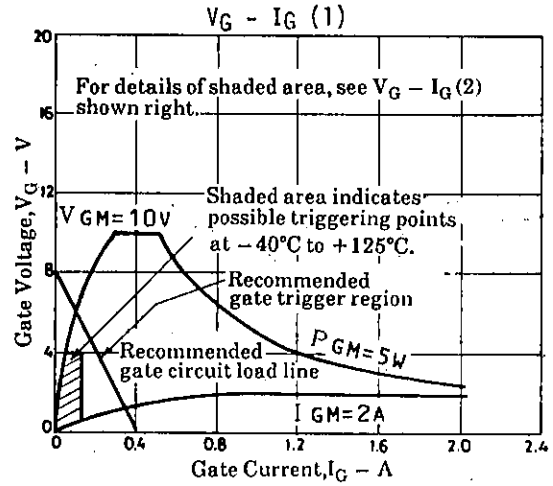
$I_T - V_T$



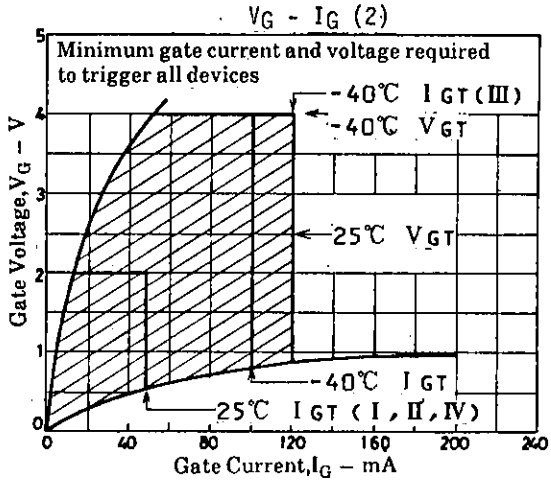
$I_{TSM} - n$



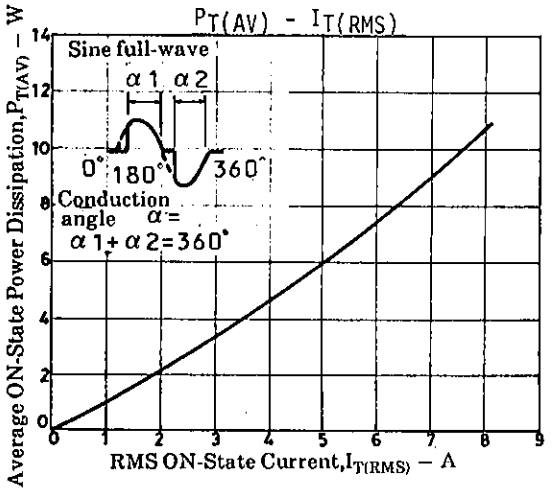
$V_G - I_G$ (1)



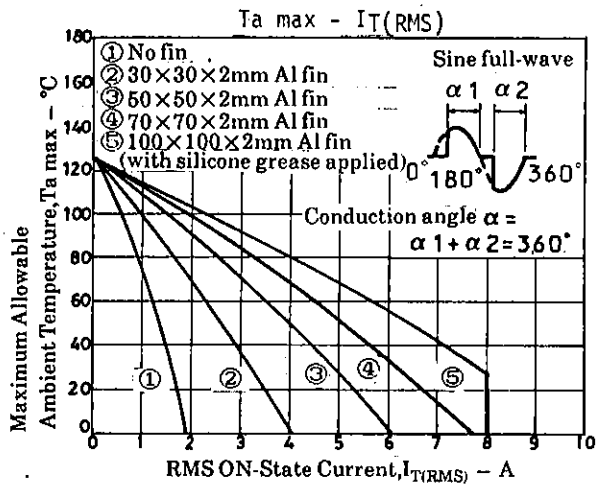
$V_G - I_G$ (2)



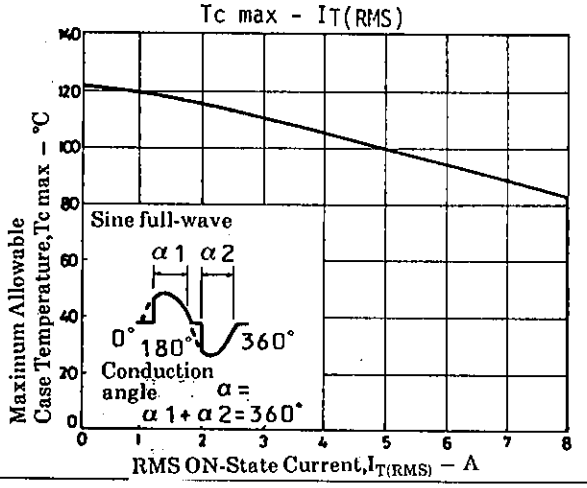
$P_{T(AV)} - I_{T(RMS)}$



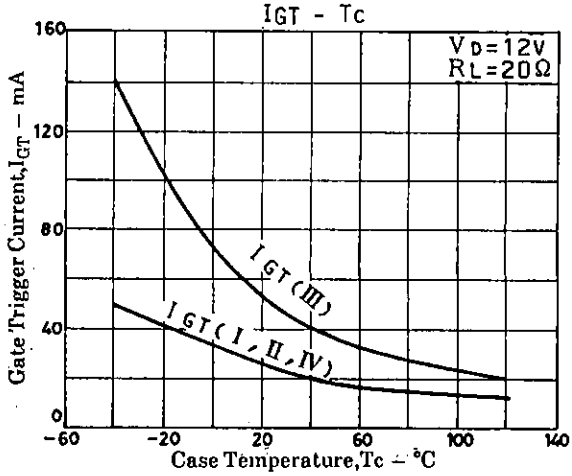
Ta max - $I_{T(RMS)}$

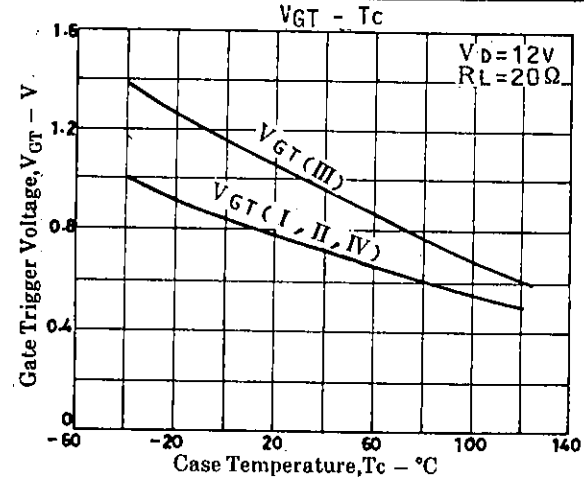


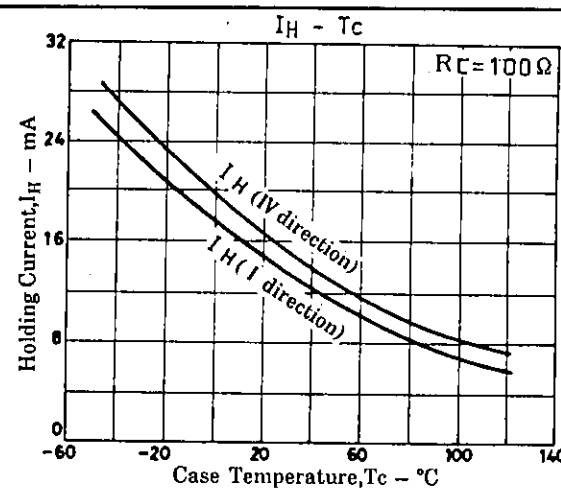
Tc max - $I_{T(RMS)}$

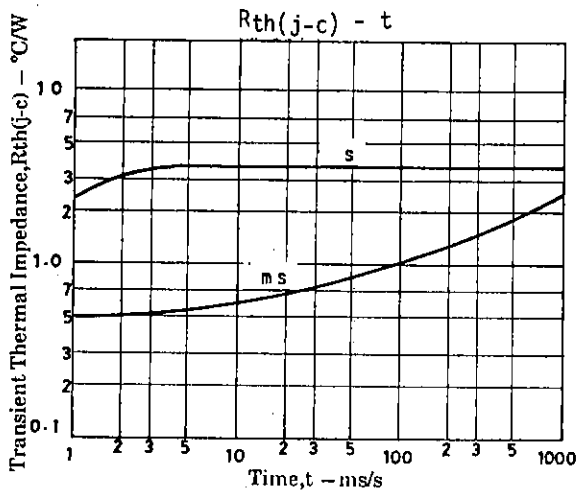


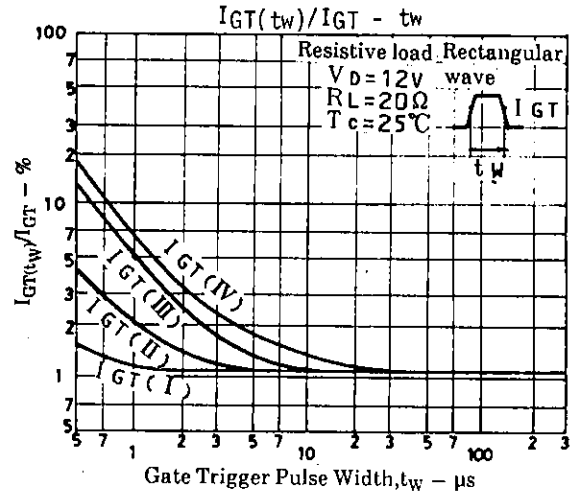
$I_{GT} - T_c$











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